



TO-92 Plastic-Encapsulate Transistors

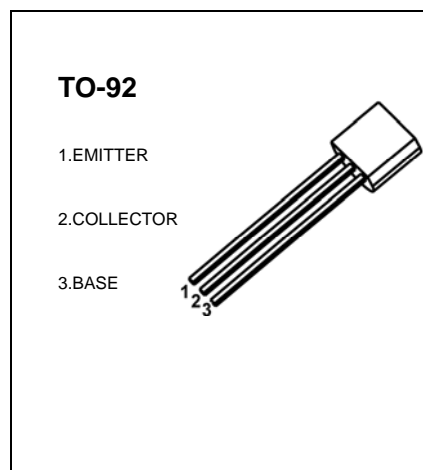
C1815 TRANSISTOR (NPN)

FEATURES

- Power dissipation

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	60	V
V _{CEO}	Collector-Emitter Voltage	50	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current -Continuous	150	mA
P _C	Collector Power Dissipation	400	mW
T _j	Junction Temperature	125	°C
T _{stg}	Storage Temperature	-55-125	°C



ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 100uA, I _E =0	60			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = 0.1mA, I _B =0	50			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = 100uA, I _C =0	5			V
Collector cut-off current	I _{CB0}	V _{CB} = 60V, I _E =0			0.1	uA
Collector cut-off current	I _{CEO}	V _{CE} = 50V, I _B =0			0.1	uA
Emitter cut-off current	I _{EBO}	V _{EB} =5V, I _C =0			0.1	uA
DC current gain	h _{FE}	V _{CE} = 6 V, I _C = 2mA	70		700	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =100mA, I _B =10mA			0.25	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =100mA, I _B =10mA			1	V
Transition frequency	f _T	V _{CE} =10 V, I _C = 1mA f=30MHz	80			MHz
Collector Output Capacitance	C _{ob}	V _{CB} =10V, I _E =0 f=1MHz			3.5	pF
Noise Figure	NF	V _{CE} =6V, I _C =0.1mA f =1KHz, R _G =10K			10	dB

CLASSIFICATION OF h_{FE}

Rank	O	Y	GR	BL
Range	70-140	120-240	200-400	350-700

Typical Characteristics

C1815

